

**Amendment under Article 34**

To: Examiner of the Patent Office, Mitsuhiro YOSHINO

**1. Identification of the International Application**

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**4. Item to be Amended    Claims**

5. Subject Matter of Amendment:

- (1) With regard to Claim 1 of Scope of claim for Patent at page 12, "A Group III nitride semiconductor light-emitting element including an n-type contact layer of n-type GaN, an n-type clad layer of n-type  $\text{Al}_x\text{Ga}_{1-x-y}\text{In}_y\text{N}$  ( $0 < x < 1$ ,  $0 \leq y < 1$ ,  $0 < x + y < 1$ ), an active layer, a p-type clad layer, and a p-type contact layer, comprising: a crack-preventing layer of n-type GaN provided between the n-type contact layer and the n-type clad layer, wherein the crack-preventing layer has a dopant concentration lower than that of the n-type contact layer." is amended to "A Group III nitride semiconductor light-emitting element including an n-type contact layer of n-type GaN, an n-type clad layer of n-type  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  ( $0 < x < 1$ ), an active layer, a p-type clad layer, and a p-type contact layer, comprising: a crack-preventing layer of n-type GaN provided between the n-type contact layer and the n-type clad layer, wherein the crack-preventing layer has a dopant concentration lower than that of the n-type contact layer."
- (2) With regard to Claim 7 of Scope of claim for Patent at pages 12-13, "A method of manufacturing a semiconductor light-emitting element having a multilayered structure constituted by sequentially stacking layers of Group III nitride semiconductors one upon another on a substrate, the method comprising: an n-type contact-layer forming step of forming an n-type contact layer of n-type GaN, and a crack-preventing layer forming step of forming a crack-preventing layer of n-type GaN, the crack-preventing layer having a dopant concentration lower than that of the n-type contact layer." is amended to "A method of manufacturing a semiconductor light-emitting element having a multilayered structure constituted by sequentially stacking layers of Group III nitride semiconductors one upon another on a substrate, the method comprising: an n-type contact-layer forming step of forming an n-type contact layer of n-type GaN, and a crack-preventing layer forming step of forming a crack-preventing layer of n-type GaN, the crack-preventing layer having a dopant

concentration lower than that of the n-type contact layer, and a clad layer forming step of forming an n-type clad layer of n-type  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  ( $0 < x < 1$ ) on the crack-preventing layer.”